Docket No. AMENDMENT TRANSMITTAL LETTER M4065.0223/P223 Art Unit Filing Date Examiner Application No. 2811 09/517,314 March 2, 2000 D. Kang Applicant(s): Chih-chen Cho vention: BACKEND METALLIZATION METHOD AND DEVICE OBTAINED THEREFROM TO THE COMMISSIONER FOR PATENTS Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below. **CLAIMS AS AMENDED** Claims Highest Number Number Remaining **Extra Claims** After Previously Present Rate Amendment Paid 0.00 **Total Claims** 23 31 Х Independent 0.00 3 4 =

Cialitis	
Multiple Dependent Claims (check if applicable)	
Other fee (please specify):	
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:	
x Large Entity Small Ent	ity
No additional fee is required for this amendment.	
Please charge Deposit Account No in the amount of \$\cap\text{A duplicate copy of this sheet is enclosed.}	··
A check in the amount of \$ to cover the filing fee is e	nclosed.
Payment by credit card. Form PTO-2038 is attached.	
The Commissioner is hereby authorized to charge and credit Deposit A as described below. A duplicate copy of this sheet is enclosed.	ccount No. <u>04-1073</u>
x Credit any overpayment.	
Charge any additional filing or application processing fees required under	er 37 CFR 1.16 and 1.17.
	September 11, 2002
Thomas J. Ó'Amico Attorney Reg. No.: 28,371	-7
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2101 L Street NW	SEP SEP
Washington, DC 20037-1526 (202) 828-2232	SEP 1



Docket No.: M4065.0223/P223 (PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Chih-Chen Cho

Application No.: 09/517,314

Filed: March 2, 2000

For: BACKEND METALLIZATION METHOD AND DEVICE OBTAINED THEREFROM

Group Art Unit: 2811

Examiner: Donghee Kang

RECEIVED
SEP 12 2002
TECHNOLOGY CENTER 2800

PRELIMINARY AMENDMENT

Box Non-Fee Amendment

Commissioner for Patents Washington, DC 20231

Dear Sir:

Prior to continued prosecution, please amend the above-identified U.S. patent application as follows:

In the Claims:

Please amend claims 1, 11, and 25 to read as follows.

1. (Twice Amended) A semiconductor device comprising:

an insulator layer;

a conductive plug positioned within said insulator layer and formed of a

single conductive material

a doped region connected to said conductive plug;

an etch-stop ayer located on said insulator layer and surrounding said plug;

1503828 v1; W8D001!.DOC